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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	154
Number of Gates	1000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1a3p1000l-pqg208i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Introduction

Contents

This user's guide contains information to help designers understand and use Microsemi's ProASIC[®]3L devices. Each chapter addresses a specific topic. Most of these chapters apply to other Microsemi device families as well. When a feature or description applies only to a specific device family, this is made clear in the text.

Revision History

The revision history for each chapter is listed at the end of the chapter. Most of these chapters were formerly included in device handbooks. Some were originally application notes or information included in device datasheets.

A "Summary of Changes" table at the end of this user's guide lists the chapters that were changed in each revision of the document, with links to the "List of Changes" sections for those chapters.

Related Information

Refer to the *ProASIC3L Flash Family FPGAs* datasheet for detailed specifications, timing, and package and pin information.

The website page for ProASIC3L devices is /www.microsemi.com/soc/products/pa3l/default.aspx.

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Global Resources in Low Power Flash Devices

Global Resource Support in Flash-Based Devices

The flash FPGAs listed in Table 3-1 support the global resources and the functions described in this document.

Table 3-1 • Flash-Based FPGAs

Series	Family [*]	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
	IGLOO nano	The industry's lowest-power, smallest-size solution
ProASIC3 ProASIC3 Low power, hi		Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex [™] -M1 soft processors, and flash memory into a monolithic device

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO products as listed in Table 3-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 3-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

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Global Resources in Low Power Flash Devices

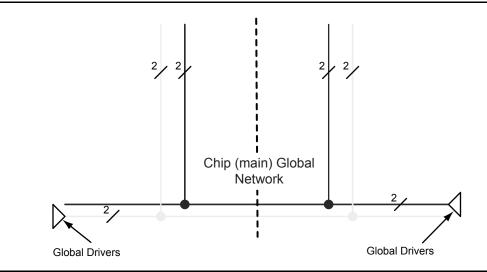


Figure 3-2 • Simplified VersaNet Global Network (30 k gates and below)

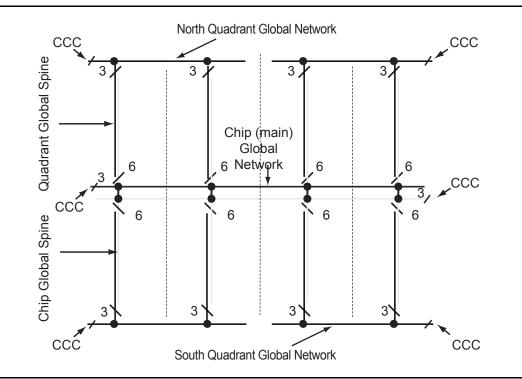


Figure 3-3 • Simplified VersaNet Global Network (60 k gates and above)

This section outlines the following device information: CCC features, PLL core specifications, functional descriptions, software configuration information, detailed usage information, recommended board-level considerations, and other considerations concerning global networks in low power flash devices.

Clock Conditioning Circuits with Integrated PLLs

Each of the CCCs with integrated PLLs includes the following:

- 1 PLL core, which consists of a phase detector, a low-pass filter, and a four-phase voltagecontrolled oscillator
- 3 global multiplexer blocks that steer signals from the global pads and the PLL core onto the global networks
- · 6 programmable delays and 1 fixed delay for time advance/delay adjustments
- 5 programmable frequency divider blocks to provide frequency synthesis (automatically configured by the SmartGen macro builder tool)

Clock Conditioning Circuits without Integrated PLLs

There are two types of simplified CCCs without integrated PLLs in low power flash devices.

- 1. The simplified CCC with programmable delays, which is composed of the following:
 - 3 global multiplexer blocks that steer signals from the global pads and the programmable delay elements onto the global networks
 - 3 programmable delay elements to provide time delay adjustments
- 2. The simplified CCC (referred to as CCC-GL) without programmable delay elements, which is composed of the following:
 - A global multiplexer block that steer signals from the global pads onto the global networks

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Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

CCC Locations

CCCs located in the middle of the east and west sides of the device access the three VersaNet global networks on each side (six total networks), while the four CCCs located in the four corners access three quadrant global networks (twelve total networks). See Figure 4-13.

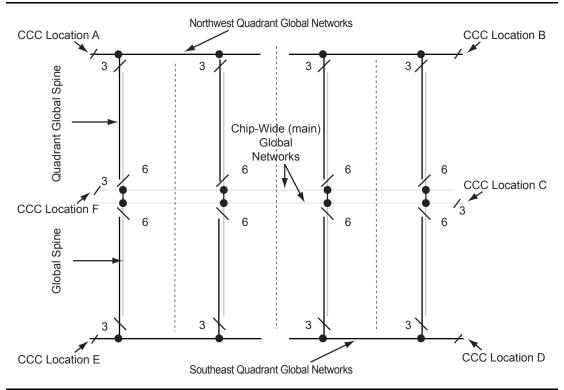


Figure 4-13 • Global Network Architecture for 60 k Gate Devices and Above

The following explains the locations of the CCCs in IGLOO and ProASIC3 devices:

In Figure 4-15 on page 98 through Figure 4-16 on page 98, CCCs with integrated PLLs are indicated in red, and simplified CCCs are indicated in yellow. There is a letter associated with each location of the CCC, in clockwise order. The upper left corner CCC is named "A," the upper right is named "B," and so on. These names finish up at the middle left with letter "F."

Table 4-9 to Table 4-15 on page 110 provide descriptions of the configuration data for the configuration bits.

Table 4-9 • Input Clock Divider, FINDIV[6:0] (/n)

FINDIV<6:0> State	Divisor	New Frequency Factor
0	1	1.00000
1	2	0.50000
:	i	
127	128	0.0078125

Table 4-10 • Feedback Clock Divider, FBDIV[6:0] (/m)

FBDIV<6:0> State	Divisor	New Frequency Factor	
0	1	1	
1	2	2	
:	:	:	
127	128	128	

Table 4-11 • Output Frequency DividersA Output Divider, OADIV <4:0> (/u);B Output Divider, OBDIV <4:0> (/v);C Output Divider, OCDIV <4:0> (/w)

OADIV<4:0>; OBDIV<4:0>; CDIV<4:0> State	Divisor	New Frequency Factor
0	1	1.00000
1	2	0.50000
:	:	:
31	32	0.03125

Table 4-12 • MUXA, MUXB, MUXC

OAMUX<2:0>; OBMUX<2:0>; OCMUX<2:0> State	MUX Input Selected
0	None. Six-input MUX and PLL are bypassed. Clock passes only through global MUX and goes directly into HC ribs.
1	Not available
2	PLL feedback delay line output
3	Not used
4	PLL VCO 0° phase shift
5	PLL VCO 270° phase shift
6	PLL VCO 180° phase shift
7	PLL VCO 90° phase shift

Conclusion

The advanced CCCs of the IGLOO and ProASIC3 devices are ideal for applications requiring precise clock management. They integrate easily with the internal low-skew clock networks and provide flexible frequency synthesis, clock deskewing, and/or time-shifting operations.

Related Documents

Application Notes

Board-Level Considerations http://www.microsemi.com/soc/documents/ALL_AC276_AN.pdf

Datasheets

Fusion Family of Mixed Signal FPGAs http://www.microsemi.com/soc/documents/Fusion_DS.pdf

User's Guides

IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide http://www.microsemi.com/soc/documents/pa3 libguide ug.pdf

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
August 2012	The "Implementing EXTFB in ProASIC3/E Devices" section is new (SAR 36647).	
	Table 4-7 • Delay Values in Libero SoC Software per Device Family was added to the "Clock Delay Adjustment" section (SAR 22709).	102
	The "Phase Adjustment" section was rewritten to explain better why the visual CCC shows both the actual phase and the actual delay that is equivalent to this phase shift (SAR 29647).	103
	The hyperlink for the <i>Board-Level Considerations</i> application note was corrected (SAR 36663)	128, 129
December 2011	Figure 4-20 • PLL Block Diagram, Figure 4-22 • CCC Block Control Bits – Graphical Representation of Assignments, and Table 4-12 • MUXA, MUXB, MUXC were revised to change the phase shift assignments for PLLs 4 through 7 (SAR 33791).	101, 105, 109
June 2011	The description for RESETEN in Table 4-8 • Configuration Bit Descriptions for the CCC Blocks was revised. The phrase "and should not be modified via dynamic configuration" was deleted because RESETEN is read only (SAR 25949).	106
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	N/A



SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

without reprogramming the device. Dynamic flag settings are determined by register values and can be altered without reprogramming the device by reloading the register values either from the design or through the UJTAG interface described in the "Initializing the RAM/FIFO" section on page 164.

SmartGen can also configure the FIFO to continue counting after the FIFO is full. In this configuration, the FIFO write counter will wrap after the counter is full and continue to write data. With the FIFO configured to continue to read after the FIFO is empty, the read counter will also wrap and re-read data that was previously read. This mode can be used to continually read back repeating data patterns stored in the FIFO (Figure 6-15).

Figure 6-15 • SmartGen FIFO Configuration Interface

FIFOs configured using SmartGen can also make use of the port mapping feature to configure the names of the ports.

Limitations

Users should be aware of the following limitations when configuring SRAM blocks for low power flash devices:

- SmartGen does not track the target device in a family, so it cannot determine if a configured memory block will fit in the target device.
- Dual-port RAMs with different read and write aspect ratios are not supported.
- Cascaded memory blocks can only use a maximum of 64 blocks of RAM.
- The Full flag of the FIFO is sensitive to the maximum depth of the actual physical FIFO block, not the depth requested in the SmartGen interface.

User I/O Naming Convention

IGLOO and ProASIC3

Due to the comprehensive and flexible nature of IGLOO and ProASIC3 device user I/Os, a naming scheme is used to show the details of each I/O (Figure 7-19 on page 207 and Figure 7-20 on page 207). The name identifies to which I/O bank it belongs, as well as pairing and pin polarity for differential I/Os.

I/O Nomenclature = FF/Gmn/IOuxwBy

Gmn is only used for I/Os that also have CCC access—i.e., global pins.

- FF = Indicates the I/O dedicated for the Flash*Freeze mode activation pin in IGLOO and ProASIC3L devices only
- G = Global
- m = Global pin location associated with each CCC on the device: A (northwest corner), B (northeast corner), C (east middle), D (southeast corner), E (southwest corner), and F (west middle)
- n = Global input MUX and pin number of the associated Global location m—either A0, A1, A2, B0, B1, B2, C0, C1, or C2. Refer to the "Global Resources in Low Power Flash Devices" section on page 47 for information about the three input pins per clock source MUX at CCC location m.
- u = I/O pair number in the bank, starting at 00 from the northwest I/O bank and proceeding in a clockwise direction
- x = P or U (Positive), N or V (Negative) for differential pairs, or R (Regular—single-ended) for the I/Os that support single-ended and voltage-referenced I/O standards only. U (Positive) or V (Negative)—for LVDS, DDR LVDS, B-LVDS, and M-LVDS only—restricts the I/O differential pair from being selected as an LVPECL pair.
- w = D (Differential Pair), P (Pair), or S (Single-Ended). D (Differential Pair) if both members of the pair are bonded out to adjacent pins or are separated only by one GND or NC pin; P (Pair) if both members of the pair are bonded out but do not meet the adjacency requirement; or S (Single-Ended) if the I/O pair is not bonded out. For Differential Pairs (D), adjacency for ball grid packages means only vertical or horizontal. Diagonal adjacency does not meet the requirements for a true differential pair.
- B = Bank
- y = Bank number (0–3). The Bank number starts at 0 from the northwest I/O bank and proceeds in a clockwise direction.

I/O Standards

Single-Ended Standards

These I/O standards use a push-pull CMOS output stage with a voltage referenced to system ground to designate logical states. The input buffer configuration, output drive, and I/O supply voltage (V_{CCI}) vary among the I/O standards (Figure 8-6).

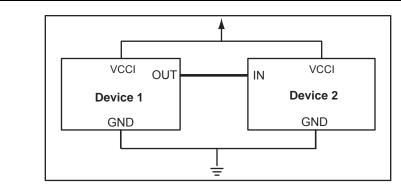


Figure 8-6 • Single-Ended I/O Standard Topology

The advantage of these standards is that a common ground can be used for multiple I/Os. This simplifies board layout and reduces system cost. Their low-edge-rate (dv/dt) data transmission causes less electromagnetic interference (EMI) on the board. However, they are not suitable for high-frequency (>200 MHz) switching due to noise impact and higher power consumption.

LVTTL (Low-Voltage TTL)

This is a general-purpose standard (EIA/JESD8-B) for 3.3 V applications. It uses an LVTTL input buffer and a push-pull output buffer. The LVTTL output buffer can have up to six different programmable drive strengths. The default drive strength is 12 mA. VCCI is 3.3 V. Refer to "I/O Programmable Features" on page 227 for details.

LVCMOS (Low-Voltage CMOS)

The low power flash devices provide four different kinds of LVCMOS: LVCMOS 3.3 V, LVCMOS 2.5 V, LVCMOS 1.8 V, and LVCMOS 1.5 V. LVCMOS 3.3 V is an extension of the LVCMOS standard (JESD8-B-compliant) used for general-purpose 3.3 V applications. LVCMOS 2.5 V is an extension of the LVCMOS standard (JESD8-5-compliant) used for general-purpose 2.5 V applications. LVCMOS 2.5 V for the 30 k gate devices has a clamp diode to VCCI, but for all other devices there is no clamp diode.

There is yet another standard supported by IGLOO and ProASIC3 devices (except A3P030): LVCMOS 2.5/5.0 V. This standard is similar to LVCMOS 2.5 V, with the exception that it can support up to 3.3 V on the input side (2.5 V output drive).

LVCMOS 1.8 V is an extension of the LVCMOS standard (JESD8-7–compliant) used for general-purpose 1.8 V applications. LVCMOS 1.5 V is an extension of the LVCMOS standard (JESD8-11–compliant) used for general-purpose 1.5 V applications.

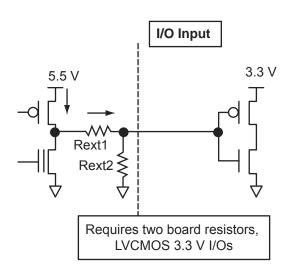
The VCCI values for these standards are 3.3 V, 2.5 V, 1.8 V, and 1.5 V, respectively. Like LVTTL, the output buffer has up to seven different programmable drive strengths (2, 4, 6, 8, 12, 16, and 24 mA). Refer to "I/O Programmable Features" on page 227 for details.

3.3 V PCI (Peripheral Component Interface)

This standard specifies support for both 33 MHz and 66 MHz PCI bus applications. It uses an LVTTL input buffer and a push-pull output buffer. With the aid of an external resistor, this I/O standard can be 5 V–compliant for low power flash devices. It does not have programmable drive strength.

3.3 V PCI-X (Peripheral Component Interface Extended)

An enhanced version of the PCI specification, 3.3 V PCI-X can support higher average bandwidths; it increases the speed that data can move within a computer from 66 MHz to 133 MHz. It is backward-



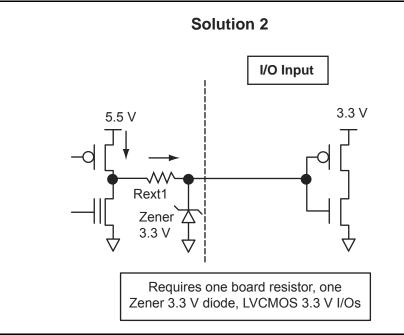
Solution 1

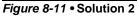
Figure 8-10 • Solution 1

Solution 2

The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.

This scheme will also work for a 3.3 V PCI/PCI-X configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the external resistors and Zener, as shown in Figure 8-11. Relying on the diode clamping would create an excessive pad DC voltage of 3.3 V + 0.7 V = 4 V.





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I/O Software Control in Low Power Flash Devices

Instantiating in HDL code

All the supported I/O macros can be instantiated in the top-level HDL code (refer to the *IGLOO*, *ProASIC3*, *SmartFusion*, *and Fusion Macro Library Guide* for a detailed list of all I/O macros). The following is an example:

```
library ieee;
use ieee.std_logic_1164.all;
library proasic3e;
entity TOP is
 port(IN2, IN1 : in std_logic; OUT1 : out std_logic);
end TOP;
architecture DEF_ARCH of TOP is
  component INBUF_LVCMOS5U
    port(PAD : in std_logic := 'U'; Y : out std_logic);
  end component;
  component INBUF_LVCMOS5
   port(PAD : in std_logic := 'U'; Y : out std_logic);
  end component;
  component OUTBUF_SSTL3_II
    port(D : in std_logic := 'U'; PAD : out std_logic);
  end component;
  Other component ....
signal x, y, z.....other signals : std_logic;
begin
  I1 : INBUF_LVCMOS5U
   port map(PAD => IN1, Y =>x);
  12 : INBUF LVCMOS5
   port map(PAD => IN2, Y => y);
  I3 : OUTBUF_SSTL3_II
    port map(D => z, PAD => OUT1);
```

other port mapping ...

end DEF_ARCH;

Synthesizing the Design

Libero SoC integrates with the Synplify[®] synthesis tool. Other synthesis tools can also be used with Libero SoC. Refer to the *Libero SoC User's Guide* or Libero online help for details on how to set up the Libero tool profile with synthesis tools from other vendors.

During synthesis, the following rules apply:

- Generic macros:
 - Users can instantiate generic INBUF, OUTBUF, TRIBUF, and BIBUF macros.
 - Synthesis will automatically infer generic I/O macros.
 - The default I/O technology for these macros is LVTTL.
 - Users will need to use the I/O Attribute Editor in Designer to change the default I/O standard if needed (see Figure 9-6 on page 259).
- Technology-specific I/O macros:
 - Technology-specific I/O macros, such as INBUF_LVCMO25 and OUTBUF_GTL25, can be instantiated in the design. Synthesis will infer these I/O macros in the netlist.

I/O Bank Resource Usage

This is an important portion of the report. The user must meet the requirements stated in this table. Figure 9-10 shows the I/O Bank Resource Usage table included in the I/O bank report:

Figure 9-10 • I/O Bank Resource Usage Table

The example in Figure 9-10 shows that none of the I/O macros is assigned to the bank because more than one VCCI is detected.

I/O Voltage Usage

The I/O Voltage Usage table provides the number of VREF (E devices only) and V_{CCI} assignments required in the design. If the user decides to make I/O assignments manually (PDC or MVN), the issues listed in this table must be resolved before proceeding to Layout. As stated earlier, VREF assignments must be made if there are any voltage-referenced I/Os.

Figure 9-11 shows the I/O Voltage Usage table included in the I/O bank report.

Figure 9-11 • I/O Voltage Usage Table

The table in Figure 9-11 indicates that there are two voltage-referenced I/Os used in the design. Even though both of the voltage-referenced I/O technologies have the same VCCI voltage, their VREF voltages are different. As a result, two I/O banks are needed to assign the VCCI and VREF voltages.

In addition, there are six single-ended I/Os used that have the same VCCI voltage. Since two banks are already assigned with the same VCCI voltage and there are enough unused bonded I/Os in



DDR for Microsemi's Low Power Flash Devices

Table 10-2 • DDR I/O Options (continued)

DDR Register Type	I/О Туре	I/O Standard	Sub-Options	Comments	
Transmit Register	Tristate	Normal	Enable Polarity	Low/high (low default)	
(continued)	Buffer	LVTTL	Output Drive	2, 4, 6, 8, 12,16, 24, 36 mA (8 mA default)	
			Slew Rate	Low/high (high default)	
			Enable Polarity	Low/high (low default)	
			Pull-Up/-Down	None (default)	
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)	
			Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)	
			Slew Rate	Low/high (high default)	
			Enable Polarity	Low/high (low default)	
			Pull-Up/-Down	None (default)	
		PCI/PCI-X	Enable Polarity	Low/high (low default)	
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)	
			Enable Polarity	Low/high (low default)	
		HSTL	Class	I / II (I default)	
			Enable Polarity	Low/high (low default)	
		SSTL2/SSTL3	Class	I / II (I default)	
			Enable Polarity	Low/high (low default)	
	Bidirectional Buffer	Normal	Enable Polarity	Low/high (low default)	
		LVTTL	Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)	
			Slew Rate	Low/high (high default)	
			Enable Polarity	Low/high (low default)	
			Pull-Up/-Down	None (default)	
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)	
			Enable Polarity	Low/high (low default)	
			Pull-Up	None (default)	
		PCI/PCI-X	None		
			Enable Polarity	Low/high (low default)	
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)	
			Enable Polarity	Low/high (low default)	
		HSTL	Class	I / II (I default)	
			Enable Polarity	Low/high (low default)	
		SSTL2/SSTL3	Class	I / II (I default)	
			Enable Polarity	Low/high (low default)	

Note: *IGLOO nano and ProASIC3 nano devices do not support differential inputs.

DDR Input Register

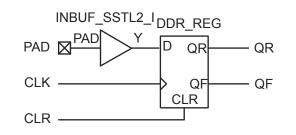


Figure 10-5 • DDR Input Register (SSTL2 Class I)

The corresponding structural representations, as generated by SmartGen, are shown below:

DDR_REG_DDR_REG_0_inst(.D(Y),.CLK(CLK),.CLR(CLR),.QR(QR),.QF(QF));

Verilog

```
module DDR_InBuf_SSTL2_I(PAD,CLR,CLK,QR,QF);
```

input PAD, CLR, CLK; output QR, QF; wire Y; INBUF_SSTL2_I INBUF_SSTL2_I_0_inst(.PAD(PAD),.Y(Y));

endmodule

VHDL

```
library ieee;
use ieee.std_logic_1164.all;
--The correct library will be inserted automatically by SmartGen
library proasic3; use proasic3.all;
--library fusion; use fusion.all;
--library igloo; use igloo.all;
entity DDR_InBuf_SSTL2_I is
  port(PAD, CLR, CLK : in std_logic; QR, QF : out std_logic) ;
end DDR_InBuf_SSTL2_I;
architecture DEF_ARCH of DDR_InBuf_SSTL2_I is
  component INBUF_SSTL2_I
    port(PAD : in std_logic := 'U'; Y : out std_logic) ;
  end component;
  component DDR_REG
   port(D, CLK, CLR : in std_logic := 'U'; QR, QF : out std_logic) ;
  end component;
signal Y : std_logic ;
begin
  INBUF_SSTL2_I_0_inst : INBUF_SSTL2_I
  port map(PAD => PAD, Y => Y);
  DDR_REG_0_inst : DDR_REG
  port map(D => Y, CLK => CLK, CLR => CLR, QR => QR, QF => QF);
end DEF_ARCH;
```



Security in Low Power Flash Devices

Figure 12-10 • All Silicon Features Selected for IGLOO and ProASIC3 Devices

Figure 12-11 • All Silicon Features Selected for Fusion

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In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X

IEEE 1532 (JTAG) Interface

The supported industry-standard IEEE 1532 programming interface builds on the IEEE 1149.1 (JTAG) standard. IEEE 1532 defines the standardized process and methodology for ISP. Both silicon and software issues are addressed in IEEE 1532 to create a simplified ISP environment. Any IEEE 1532 compliant programmer can be used to program low power flash devices. Device serialization is not supported when using the IEEE1532 standard. Refer to the standard for detailed information about IEEE 1532.

Security

Unlike SRAM-based FPGAs that require loading at power-up from an external source such as a microcontroller or boot PROM, Microsemi nonvolatile devices are live at power-up, and there is no bitstream required to load the device when power is applied. The unique flash-based architecture prevents reverse engineering of the programmed code on the device, because the programmed data is stored in nonvolatile memory cells. Each nonvolatile memory cell is made up of small capacitors and any physical deconstruction of the device will disrupt stored electrical charges.

Each low power flash device has a built-in 128-bit Advanced Encryption Standard (AES) decryption core, except for the 30 k gate devices and smaller. Any FPGA core or FlashROM content loaded into the device can optionally be sent as encrypted bitstream and decrypted as it is loaded. This is particularly suitable for applications where device updates must be transmitted over an unsecured network such as the Internet. The embedded AES decryption core can prevent sensitive data from being intercepted (Figure 13-1 on page 331). A single 128-bit AES Key (32 hex characters) is used to encrypt FPGA core programming data and/or FlashROM programming data in the Microsemi tools. The low power flash devices also decrypt with a single 128-bit AES Key. In addition, low power flash devices support a Message Authentication Code (MAC) for authentication of the encrypted bitstream on-chip. This allows the encrypted bitstream to be authenticated and prevents erroneous data from being programmed into the device. The FPGA core, FlashROM, and Flash Memory Blocks (FBs), in Fusion only, can be updated independently using a programming file that is AES-encrypted (cipher text) or uses plain text.

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In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X

- 3. A single STAPL file or multiple STAPL files with multiple FlashROM contents. A single STAPL file will be generated if the device serialization feature is not used. You can program the whole FlashROM or selectively program individual pages.
- 4. A single STAPL file to configure the security settings for the device, such as the AES Key and/or Pass Key.

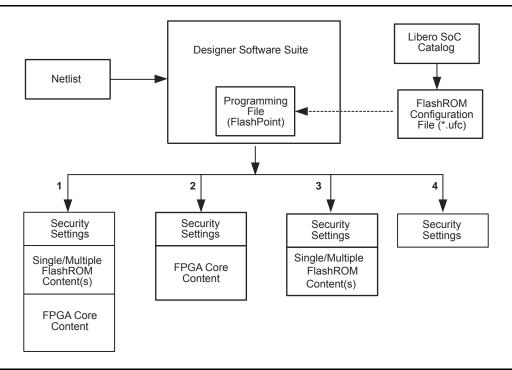


Figure 13-4 • Flexible Programming File Generation for Different Applications

Programming Solution

For device programming, any IEEE 1532–compliant programmer can be used; however, the FlashPro4/3/3X programmer must be used to control the low power flash device's rich security features and FlashROM programming options. The FlashPro4/3/3X programmer is a low-cost portable programmer for the Microsemi flash families. It can also be used with a powered USB hub for parallel programming. General specifications for the FlashPro4/3/3X programmer are as follows:

- Programming clock TCK is used with a maximum frequency of 20 MHz, and the default frequency is 4 MHz.
- Programming file STAPL
- Daisy chain Supported. You can use the ChainBuilder software to build the programming file for the chain.
- Parallel programming Supported. Multiple FlashPro4/3/3X programmers can be connected together using a powered USB hub or through the multiple USB ports on the PC.
- Power supply The target board must provide VCC, VCCI, VPUMP, and VJTAG during programming. However, if there is only one device on the target board, the FlashPro4/3/3X programmer can generate the required VPUMP voltage from the USB port.

Brownout Voltage

Brownout is a condition in which the voltage supplies are lower than normal, causing the device to malfunction as a result of insufficient power. In general, Microsemi does not guarantee the functionality of the design inside the flash FPGA if voltage supplies are below their minimum recommended operating condition. Microsemi has performed measurements to characterize the brownout levels of FPGA power supplies. Refer to Table 18-3 for device-specific brownout deactivation levels. For the purpose of characterization, a direct path from the device input to output is monitored while voltage supplies are lowered gradually. The brownout point is defined as the voltage level at which the output stops following the input. Characterization tests performed on several IGLOO, ProASIC3L, and ProASIC3 devices in typical operating conditions showed the brownout voltage levels to be within the specification.

During device power-down, the device I/Os become tristated once the first supply in the power-down sequence drops below its brownout deactivation voltage.

Table 18-3 • Brownout Deactivation Levels for VCC and VCCI

Devices	VCC Brownout Deactivation Level (V)	VCCI Brownout Deactivation Level (V)
ProASIC3, ProASIC3 nano, IGLOO, IGLOO nano, IGLOO PLUS and ProASIC3L devices running at VCC = 1.5 V	0.75 V ± 0.25 V	0.8 V ± 0.3 V
IGLOO, IGLOO nano, IGLOO PLUS, and ProASIC3L devices running at VCC = 1.2 V	0.75 V ± 0.2 V	0.8 V ± 0.15 V

PLL Behavior at Brownout Condition

When PLL power supply voltage and/or V_{CC} levels drop below the V_{CC} brownout levels mentioned above for 1.5 V and 1.2 V devices, the PLL output lock signal goes LOW and/or the output clock is lost. The following sections explain PLL behavior during and after the brownout condition.

VCCPLL and VCC Tied Together

In this condition, both VCC and VCCPLL drop below the 0.75 V (\pm 0.25 V or \pm 0.2 V) brownout level. During the brownout recovery, once VCCPLL and VCC reach the activation point (0.85 \pm 0.25 V or \pm 0.2 V) again, the PLL output lock signal may still remain LOW with the PLL output clock signal toggling. If this condition occurs, there are two ways to recover the PLL output lock signal:

- 1. Cycle the power supplies of the PLL (power off and on) by using the PLL POWERDOWN signal.
- 2. Turn off the input reference clock to the PLL and then turn it back on.

Only VCCPLL Is at Brownout

In this case, only VCCPLL drops below the 0.75 V (\pm 0.25 V or \pm 0.2 V) brownout level and the VCC supply remains at nominal recommended operating voltage (1.5 V \pm 0.075 V for 1.5 V devices and 1.2 V \pm 0.06 V for 1.2 V devices). In this condition, the PLL behavior after brownout recovery is similar to initial power-up condition, and the PLL will regain lock automatically after VCCPLL is ramped up above the activation level (0.85 \pm 0.25 V or \pm 0.2 V). No intervention is necessary in this case.

Only VCC Is at Brownout

In this condition, VCC drops below the 0.75 V (\pm 0.25 V or \pm 0.2 V) brownout level and VCCPLL remains at nominal recommended operating voltage (1.5 V \pm 0.075 V for 1.5 V devices and 1.2 V \pm 0.06 V for 1.2 V devices). During the brownout recovery, once VCC reaches the activation point again (0.85 \pm 0.25 V or \pm 0.2 V), the PLL output lock signal may still remain LOW with the PLL output clock signal toggling. If this condition occurs, there are two ways to recover the PLL output lock signal:

- 1. Cycle the power supplies of the PLL (power off and on) by using the PLL POWERDOWN signal.
- 2. Turn off the input reference clock to the PLL and then turn it back on.

It is important to note that Microsemi recommends using a monotonic power supply or voltage regulator to ensure proper power-up behavior.

B – **Product Support**

Microsemi SoC Products Group backs its products with various support services, including Customer Service, Customer Technical Support Center, a website, electronic mail, and worldwide sales offices. This appendix contains information about contacting Microsemi SoC Products Group and using these support services.

Customer Service

Contact Customer Service for non-technical product support, such as product pricing, product upgrades, update information, order status, and authorization.

From North America, call 800.262.1060 From the rest of the world, call 650.318.4460 Fax, from anywhere in the world, 650.318.8044

Customer Technical Support Center

Microsemi SoC Products Group staffs its Customer Technical Support Center with highly skilled engineers who can help answer your hardware, software, and design questions about Microsemi SoC Products. The Customer Technical Support Center spends a great deal of time creating application notes, answers to common design cycle questions, documentation of known issues, and various FAQs. So, before you contact us, please visit our online resources. It is very likely we have already answered your questions.

Technical Support

Visit the Customer Support website (www.microsemi.com/soc/support/search/default.aspx) for more information and support. Many answers available on the searchable web resource include diagrams, illustrations, and links to other resources on the website.

Website

You can browse a variety of technical and non-technical information on the SoC home page, at www.microsemi.com/soc.

Contacting the Customer Technical Support Center

Highly skilled engineers staff the Technical Support Center. The Technical Support Center can be contacted by email or through the Microsemi SoC Products Group website.

Email

You can communicate your technical questions to our email address and receive answers back by email, fax, or phone. Also, if you have design problems, you can email your design files to receive assistance. We constantly monitor the email account throughout the day. When sending your request to us, please be sure to include your full name, company name, and your contact information for efficient processing of your request.

The technical support email address is soc_tech@microsemi.com.